L Number	Hits	Search Text	DB	Time stamp
1	0	microcircuit and stacked and encapsulant	USPAT;	2003/03/12
		and encasing and removing near insulation	US-PGPUB;	12:16
			EPO; JPO;	
			DERWENT;	•
	;		IBM_TDB	
2	0	microcircuit and stacked and encapsulant	USPAT;	2003/03/12
_	_	and removing near insulation	US-PGPUB;	12:17
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
3	0	microcircuit and PEM and encapsulant and	USPAT;	2003/03/12
-		removing near insulation	US-PGPUB;	12:17
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
4	0	PEM and encapsulant and removing near	USPAT;	2003/03/12
		insulation	US-PGPUB;	12:17
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
5	0	PEM and removing near insulation	USPAT;	2003/03/12
			US PGPUB:	12:17
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
6	2601	PEM	USPAT;	2003/03/12
			US-PGPUB;	12:17
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
7	80	(PEM) and encapsulation	USPAT;	2003/03/12
			US-PGPUB;	12:18
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
8	29	(PEM) and encapsulation and removing	USPAT;	2003/03/12
			US-PGPUB;	12:18
			EPO; JPO;	•
			DERWENT;	
•			IBM_TDB	
9	394917	(PEM) and removing insulation	USPAT;	2003/03/12
			US-PGPUB;	12:20
		_	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
10	0	(PEM) and removing near insulation	USPAT;	2003/03/12
		_	US-PGPUB;	12:20
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	,

	ı		HODAT	0000/00/40
11	0	(PEM) and removing near encapsulant	USPAT;	2003/03/12
			US-PGPUB;	12:21
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
12	2	(PEM) and removing same encapsulant	USPAT;	2003/03/12
		•	US-PGPUB;	12:30
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
13	o	20020119605.URPN.	USPAT	2003/03/12
13		20020119003.0RFN.	USPAI	12:22
		(1) 40 4 7 40 7 11 11 44 40 0 0 411 1 11 4 40 0 40 0	LICDAT	
14	21	("4017495" "4118861" "4490496"	USPAT	2003/03/12
		"4729062" "4826756" "4830922"		12:22
		"4902769" "4920639" "4991286"		
		"5274913" "5381304" "5405807"		
		"5434751" "5512613" "5560934"		
		"5600181" "5641546" "5685071"		
•		"5828126" "5858943" "6111323").PN.		
15	41	("3801880" "3864426" "4012832"	USPAT	2003/03/12
		"4370292" "4529755" "4604444"		12:24
		"4626556" "4632798" "4663190"		12.27
		• • • • • • • • • • • • • • • • • • • •		
		"4729062" "4738892" "4983683"		
		"4985751" "5037779" "5043211"		
		"5061657" "5064895" "5072874"		
•		"5120678" "5128204" "5140068"		
•	1	"5160786" "5199163" "5250848"		
		"5264520" "5274913" "5286572"		
		"5298548" "5300625" "5313365"		
		"5326413" "5371328" "5381304"		
		"5434751" "5457149" "5460767"		
		"5471096" "5474620" "5498689"		
		"5821456" "5863664").PN.		
16	0	(PEM) and removing and grinding near	USPAT;	2003/03/12
10		encapsulant	US-PGPUB;	12:31
		encapsulant	*	12.31
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
17	0	(PEM) and removing and grinding near	USPAT;	2003/03/12
		(encapsulant or insulation)	US-PGPUB;	12:32
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
18	6	removing and grinding near (encapsulant or	USPAT;	2003/03/12
		insulation)	US-PGPUB;	12:33
			EPO; JPO;	
			DERWENT;	
			1	
40			IBM_TDB	0000100140
19	1	IC and grinding near (encapsulant or	USPAT;	2003/03/12
		insulation)	US-PGPUB;	12:36
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

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20 0 8153696.URPN. USPAT 2003/03/ 12:34 21 1 1996-331608.NRAN. DERWENT 2003/03/ 12:34 22 552166 29/\$.ccls. grinding near encapsulant or USPAT; 2003/03/	12
21 1 1996-331608.NRAN. DERWENT 2003/03/12:34	
12:34	
	12
22 552166 29/\$.ccis. grinding near encapsulant or USPA1; 2003/03/	12
insulation US DCDUD: 40-20	
insulation US-PGPUB; 12:36 EPO; JPO;	į
DERWENT;	
IBM TDB	
23 166292 29/\$.ccls. grinding near (encapsulant or USPAT; 2003/03/	12
insulation) US-PGPUB; 12:37	-
EPO; JPO;	
DERWENT;	
IBM_TDB	
24 29/\$.ccls. and grinding near (encapsulant USPAT; 2003/03/	12
or insulation) US-PGPUB; 12:37	
EPO; JPO;	
DERWENT;	
IBM_TDB	
25	12
US-PGPUB; 12:38	
EPO; JPO;	
DERWENT;	
IBM_TDB	
26 28 29/840.ccls. and microcircuit USPAT; 2003/03/	12
US-PGPUB; 12:39 EPO; JPO;	
DERWENT;	
IBM_TDB	
27 3 29/840.ccls. and microcircuit and USPAT; 2003/03/	12
encapsulant US-PGPUB; 12:42	
EPO; JPO;	
DERWENT;	
IBM_TDB	
28 0 20020126459.URPN. USPAT 2003/03/	12
12:42	
29 2 "Stackable microcircuit layer" USPAT; 2003/03/	12
US-PGPUB; 12:43	
EPO; JPO;	
DERWENT;	
IBM_TDB	40
30 1 "Stackable microcircuit" and 174/52.2.ccls. USPAT; 2003/03/	12
US-PGPUB; 12:43	
EPO; JPO; DERWENT;	ļ
IBM_TDB	
31 4077 "Stackable microcircuit layer "and USPAT; 2003/03/	12
(361/743;29/830 ;29/840 ;29/841 ;361/735 US-PGPUB; 12:44	-
;361/746).ccls. EPO; JPO;	
DERWENT;	
IBM_TDB	

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			HODAT.	0000/00/40
32	0	"Stackable microcircuit layer" and (361/743;29/830 ;29/840 ;29/841 ;361/735 ;361/746).ccls. and grinding and removing	USPAT; US-PGPUB; EPO; JPO;	2003/03/12 12:45
		and encasing	DERWENT;	
33	1	"Stackable microcircuit layer" and	USPAT;	2003/03/12
		(361/743;29/830 ;29/840 ;29/841 ;361/735	US-PGPUB;	12:45
		;361/746).ccls. and grinding and removing	EPO; JPO;	
			DERWENT; IBM_TDB	
34	1	"Stackable microcircuit layer" and	USPAT;	2003/03/12
		(361/743;29/830 ;29/840 ;29/841 ;361/735	US-PGPUB;	12:45
		;361/746).ccls. and removing	EPO; JPO;	
			DERWENT;	
	00		IBM_TDB	2002/02/42
35	23	microcircuit and (361/743;29/830 ;29/840 ;29/841 ;361/735 ;361/746).ccls. and	USPAT; US-PGPUB;	2003/03/12 12:48
-		removing	EPO; JPO;	12.40
		Tellioving	DERWENT;	
			IBM_TDB	
36	4	(361/743;29/830 ;29/840 ;29/841 ;361/735	USPAT;	2003/03/12
		;361/746).ccls. and encapsulant near	US-PGPUB;	13:07
}		removing	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
37	17	("3903590" "4466181" "4783695"	USPAT	2003/03/12
		"4835704" "4878991" "4933042"		12:52
		"5019946" "5048179" "5091769" "5108825" "5139969" "5144747"		
		"5151776" "5154793" "5155068"		
		"5161093" "5255431").PN.		
38	8	("3702464" "4532419" "4603249"	USPAT	2003/03/12
ĺ		"4725924" "4774633" "4803542"		13:03
		"4822989" "4931853").PN.		
39	10	("5207864" "5386624" "5406025"	USPAT	2003/03/12
		"5483421" "5638597" "5739053"		13:05
		"5785234" "5813115" "5816478"		
40	6	"5873161").PN.	USPAT	2003/03/12
40	0	("3676745" "5323295" "5365403" "5367439" "5467251" "5644103").PN.	USPAI	13:06
41	60	encapsulant near removal	USPAT;	2003/03/12
			US-PGPUB;	13:10
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
42	0	20010039120.URPN.	USPAT	2003/03/12
40				13:08
43	14	encapsulant near remove and pad and wire	USPAT;	2003/03/12
			US-PGPUB;	13:13
			EPO; JPO; DERWENT;	
			·	i

	·			
44	15	("4281031" "4344809" "4359360" "4826556" "5252179" "5254237" "5271798" "5321222" "5350737" "5521360" "5552112" "5648038"	USPAT	2003/03/12 13:12
	_	"5766496" "6011249" "6211499") .PN.		
45	4	("3469053" "5268548" "5644837" "5725762").PN.	USPAT	2003/03/12 13:13
46	27	encapsulant and encasing and removing	USPAT;	2003/03/12
		and semiconductor near device	US-PGPUB; EPO; JPO; DERWENT;	13:19
			IBM_TDB	
47	19	("4143456" "4264917" "4300153" "4358552" "4507675" "4642671" "4931852" "4961107" "5101465" "5173764" "5194930" "5379186"	USPAT	2003/03/12 13:15
		"5434105" "5436203" "5450283" "5488254" "5489538" "5489801" "5866953").PN.		
48	0	encapsulant and encasing near removing and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/12 13:19
49	0	encapsulant and encasing near removing	IBM_TDB USPAT; US-PGPUB;	2003/03/12 13:19
			EPO; JPO; DERWENT; IBM_TDB	13.15
50	79	encapsulant near removing	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/12 13:26
51	11	("4460537" "4615857" "4910581" "5417826" "5434750" "5542171" "5557150" "5635671" "5656549" "5780933" "5963792").PN.	USPAT	2003/03/12 13:24
52	14	("4460537" "4615857" "4784974" "4910581" "5417826" "5434750" "5542171" "5557150" "5620928" "5625235" "5635671" "5656549" "5708567" "5756380").PN.	USPAT	2003/03/12 13:25
53	0	"removing said encapsulant"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/12 13:30
54	0	encapsulant near grinding and semiconductor near device	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/12 13:31

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55	4103	grinding and semiconductor near device	USPAT;	2003/03/12
			US-PGPUB;	13:32
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
56	10	removing and grinding and encapsulant	USPAT;	2003/03/12
		near material and semiconductor near	US-PGPUB;	13:35
		device	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
57	0	20030006494.URPN.	USPAT	2003/03/12
				13:34
58	15	grinding and encapsulant near material and	USPAT;	2003/03/12
		semiconductor near device	US-PGPUB;	13:35
	1		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
59	33	grinding and encapsulant near material and	USPAT;	2003/03/12
		semiconductor	US-PGPUB;	13:36
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
60	8	("5471087" "5773323" "5855727"	USPAT	2003/03/12
		"5863810" "5897338" "5932061"	}	13:39
		"6069392" "6136212").PN.		
61	23	("H001379" "3482419" "3627901"	USPAT	2003/03/12
		"3762039" "3969813" "4089704"		13:46
		"4359360" "4384917" "4474621"		
		"4567006" "4691225" "4768286"		
		"4914813" "4980019" "5041396"		
		"5138430" "5149662" "5155068"		
		"5180093" "5252179" "5398926"		
		"5406117" "5424254").PN.		
62	19	5424254.URPN.	USPAT	2003/03/12
				13:49